Nucleation in polycrystalline thin films using a preconditioned finite element method

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INTRODUCTION

The dynamic response of a 80 nm x 400 nm x 25 nm Co element with and without polycrystalline grains is calculated. In polycrystalline thin film elements the nucleation of reversed domains occurs randomly at grain boundaries and sharp edges. The numerical method combines a finite element scheme for space discretization with an advanced time integration scheme for the LLG equation. The use of appropriate preconditioners for the linear equations considerably reduces the computation time.



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